

Attorney Docket No.: 422.05

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Sheet 1 of 1

FORM PTO-1449 (Rev. 7-80) Trademark Office	U.S. Dept. of Commerce Patent and Trademark Office	App. Docket No. 422.05	Appl. No. 10/050,654
LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)		Applicant: CHEN, Ling, et al	
		Filing Date: Jan 16, 2002	

	Document Number	Date	Name	Class	Subclass	Filing Date
THM	4,058,430	15-Nov-1977	Method For Producing Compound Thin Films			25-Nov-1977
	4,389,973	28-Jun-1983	Apparatus For Performing Growth of Compound Thin Films			11-Dec-1983
	4,413,022	1-Nov-1983	Method For Performing Growth of Compound Thin Films			21-Jun-1979
	4,767,494	30-Aug-1988	Preparation process of compound semiconductor			19-Sep-1986
	4,806,321	21-Feb-1989	Use of infrared radiation and an ellipsoidal reflection mirror			25-Jul-1985
	4,840,921	20-Jun-1989	Process for the growth of III-V group compound semiconductor crystal on a Si substrate			30-Jun-1988
	4,845,049	4-Jul-1989	Doping III-V compound semiconductor devices with group VI monolayers using ALE			28-Mar-1988
	4,859,627	22-Aug-1989	Group VI doping of III-V semiconductors during ALE			1-Jul-1988
	4,861,417	29-Aug-1989	Method of growing group III-V compound semiconductor epitaxial layer			24-Mar-1988
	4,876,218	24-Oct-1989	Method of growing GaAs films on Si or GaAs substrates using ALE			26-Sep-1988
	4,993,357	19-Feb-1991	Apparatus for atomic layer epitaxial growth			21-Dec-1989
	5,082,798	21-Jan-1992	Crystal growth method			27-Sep-1990
	5,130,269	14-Jul-1992	Hetero-epitaxially grown compound semiconductor substrate and a method of growing the same			25-Apr-1989
	5,166,092	24-Nov-1992	Method of growing compound semiconductor epitaxial layer by atomic layer epitaxy			30-Oct-1990
	5,225,366	6-Jul-1993	Apparatus For and a Method of Growing Thin Films Elemental Semiconductors			22-Jun-1990
	5,250,148	5-Oct-1993	Process for growing GaAs monocrystal film			12-Nov-1991
	5,256,244	26-Oct-1993	Production of diffuse reflective coatings by atomic layer epitaxy			10-Feb-1992
	5,270,247	14-Dec-1993	Atomic layer epitaxy of compound semiconductor			8-Jul-1992
	5,278,435	11-Jan-1994	High responsivity ultraviolet gallium nitride detector			8-Jun-1992
	5,281,274	25-Jan-1994	Atomic Layer Epitaxy (ALE) Apparatus For Growing Thin Films of Elemental Semiconductors			4-Feb-1993
	5,290,748	1-Mar-1994	Polymerization catalyst for olefines			16-Jul-1992
	5,294,286	15-Mar-1994	Process for forming a thin film of silicon			12-Jan-1993
	5,300,186	5-Apr-1994	Hetero-epitaxially grown compound semiconductor substrate and a method of growing the same			7-Apr-1992
THM	5,316,793	31-May-1994	Directed Effusive Beam Atomic Layer Epitaxy System and Method			27-Jul-1992

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THM	5,330,610	19-Jul-1994	Method of Digital Epitaxy by Externally Controlled Closed-Loop Feedback			28-May-1993
	5,336,324	9-Aug-1994	Apparatus for depositing a coating on a substrate			4-Dec-1991
	5,338,389	16-Aug-1994	Method of epitaxially growing compound crystal and doping method therein			21-Apr-1993
	5,374,570	20-Dec-1994	Method of manufacturing active matrix display device using insulation layer formed by the ale method			19-Aug-1995
	5,395,791	7-Mar-1995	Growth of II VI laser diodes with quantum wells by atomic layer epitaxy and migration enhanced epitaxy			20-Oct-1993
	5,438,952	8-Aug-1995	Method of growing a semiconductor layer			31-Jan-1994
	5,443,033	22-Aug-1995	Semiconductor crystal growth method			11-Mar-1994
	5,458,084	17-Oct-1995	X-ray wave diffraction optics constructed by atomic layer epitaxy			9-Dec-1993
	5,480,818	2-Jan-1996	Method for forming a film and method for manufacturing a thin film transistor			9-Feb-1993
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	5,483,919	16-Jan-1996	Atomic layer epitaxy method and apparatus			17-Aug-1994
	5,484,664	16-Jan-1996	Hetero-epitaxially grown compound semiconductor substrate			21-Jan-1994
	5,532,511	2-Jul-1996	Semiconductor device comprising a highspeed static induction transistor			23-Mar-1995
	5,637,530	10-Jun-1997	II-VI compound semiconductor epitaxial layers having low defects, method for producing and devices utilizing same			10-Jun-1996
	5,693,139	2-Dec-1997	Growth of doped semiconductor monolayers			15-Jun-1993
	5,705,224	6-Jan-1998	Vapor Depositing Method			31-Jan-1995
	5,711,811	27-Jan-1998	Method and Equipment For Growing Thin Films			28-Nov-1995
	5,730,802	24-Mar-1998	Vapor growth apparatus and vapor growth method capable of growing a compound semiconductor layer having an evenness and an interfacial sharpness in units of atomic layers with good productivity			27-Dec-1996
	5,744,192	28-Apr-1998	Method of using water vapor to increase the conductivity of copper deposited with CU(HFAC) TMVS			8-Nov-1996
	5,851,849	22-Dec-1998	Process for Passivating Semiconductor Laser Structures with Severe Steps in Surface Topography			22-May-1997
	5,855,680	5-Jan-1999	Apparatus For Growing Thin Films			28-Nov-1995
	5,879,459	9-Mar-1999	Vertically-stacked process reactor and cluster tool system for atomic layer deposition			29-Aug-1997
	5,916,365	29-Jun-1999	Sequential Chemical Vapor Deposition			16-Aug-1996
	6,015,590	18-Jan-2000	Method for growing thin films			28-Nov-1995
	6,025,627	15-Feb-2000	Alternate method and structure for improved floating gate tunneling devices			29-May-1998
THM	6,036,773	14-Mar-2000	Method for growing Group III atomic			27-Mar-1997

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7Am	6,042,652	28-Mar-2000	Atomic layer deposition apparatus for depositing atomic layer on multiple substrates			7-Sep-1999
	6,043,177	28-Mar-2000	Modification of zeolite or molecular sieve membranes using atomic layer controlled chemical vapor deposition			21-Jan-1999
	6,090,442	18-Jun-2000	Method of growing films on substrates at room temperatures using catalyzed binary reaction sequence chemistry			2-Oct-1997
	6,110,530	29-Aug-2000	CVD method of depositing copper films by using improved organocopper precursor blend			25-Jun-1999
	6,113,977	5-Sep-2000	Method of growing a ZnS:Mn phosphor layer for use in thin-film electroluminescent components			11-Sep-1997
	6,124,158	26-Sep-2000	Method of reducing carbon contamination of a thin dielectric film by using gaseous organic precursors, inert gas, and ozone to react with carbon contaminants			8-Jun-1999
	6,124,158	26-Sep-2000	Formation of thin dielectric film on semiconductor substrate, includes introducing gaseous organic precursor to form bonded reactant, introducing second gaseous reactant into the reaction chamber with the bonded reactant			8-Jun-1999
	6,130,147	10-Oct-2000	Methods for forming group III-V arsenide-nitride semiconductor materials			18-Mar-1997
	6,139,700	31-Oct-2000	Method of and apparatus for forming a metal interconnection in the contact hole of a semiconductor device			30-Sep-1998
	6,143,659	7-Nov-2000	Method for manufacturing aluminum metal interconnection layer by atomic layer deposition method			27-Aug-1998
	6,174,377	16-Jan-2001	Processing Chamber for Atomic Layer Deposition Processes			4-Jan-1999
	6,174,809	16-Jan-2001	Method for forming metal layer using atomic layer deposition			15-Dec-1998
	6,197,683	6-Mar-2001	Method of forming metal nitride film by chemical vapor deposition and method of forming metal contact of semiconductor device using the same			18-Sep-1998
	6,200,893	13-Mar-2001	Radical-assisted Sequential CVD			11-Mar-1999
	6,203,613	20-Mar-2001	Atomic layer deposition with nitrate containing precursors			19-Oct-1999
	6,207,302	27-Mar-2001	Electroluminescent device and method of producing the same			2-Mar-1998
	6,248,605	19-Jun-2001	Method of growing thin film electroluminescent structures			2-Jun-1999
	6,270,572	7-Aug-2001	Method for manufacturing thin film using atomic layer deposition			9-Aug-1999
	6,287,965	11-Sep-2001	Method of forming metal layer using atomic layer deposition and semiconductor device having the metal layer as barrier metal layer or upper or lower electrode of capacitor			23-Feb-2000
	6,291,876	18-Sep-2001	Electronic devices with composite atomic barrier film and process for making same			20-Aug-1998
7Am	6,305,314	23-Oct-2001	Apparatus and concept for			17-Dec-1999

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			minimizing parasitic chemical vapor deposition during atomic layer deposition			
Thm	6,306,216	23-Oct-2001	Apparatus for deposition of thin films on wafers through atomic layer epitaxial process	11	11	12-Jul-2000
Thm	6,316,098	13-Nov-2001	Molecular layer epitaxy method and compositions			23-Mar-1999

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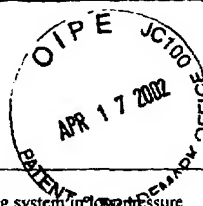
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T. Suntola and M. Simpson Atomic Layer Epitaxy	Blackie and Son	1990
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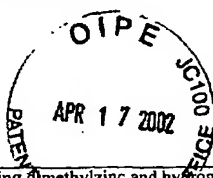
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